
ERÖFFNUNG DES INNOVATIONSZENTRUMS ADAPTSYS

Höchstintegrierte Leistungselektronik mit hoher Zuverlässigkeit

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Leistungselektronik

Agenda

- Motivation
- Schlüsselinnovationen in den aktuellen Demonstratoren
- Heterogene Integration als nächste Innovation
- Aussichtsreiche Technologien
- Resumé

Motivation

Leistungselektronik kann Energie mit unübertroffenem Wirkungsgrad in die benötigte Form bringen, damit

- ist sie ein Schlüsselement für die dezentrale Energieerzeugung und die Reduktion des Energieverbrauchs

Ziel muss sein, den Aufwand für ihre Herstellung so weit wie möglich zu reduzieren, um den massenhaften Einsatz zu forcieren

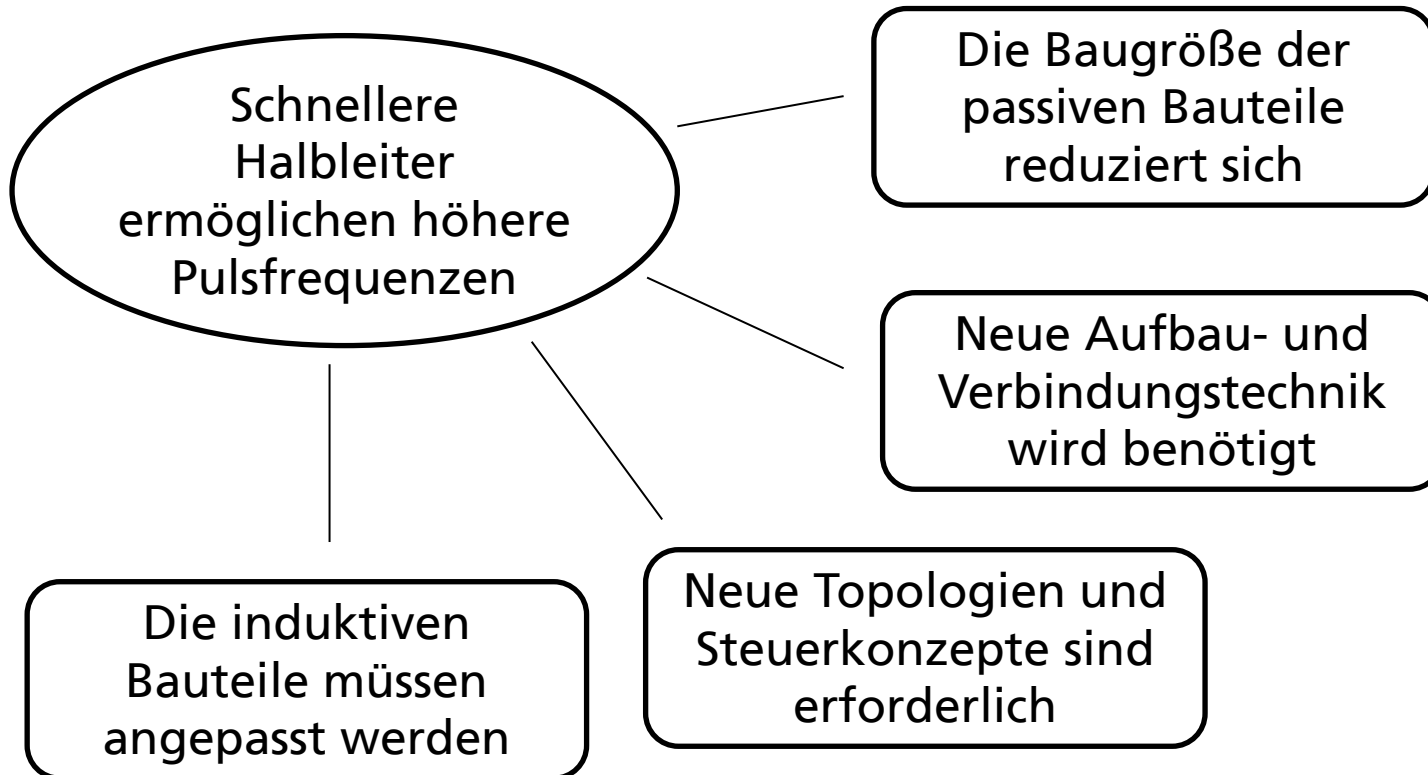


IZM Gen.1 (2012)
SiC JFets, 48 kHz pulse frequency
18l - 18,4 kg (15kW)
Conventional Packaging



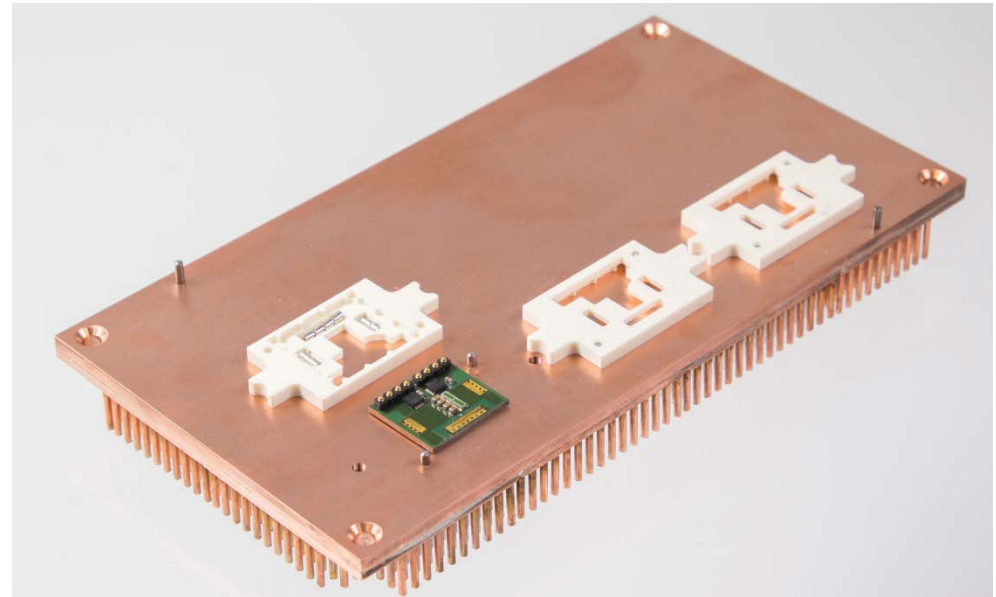
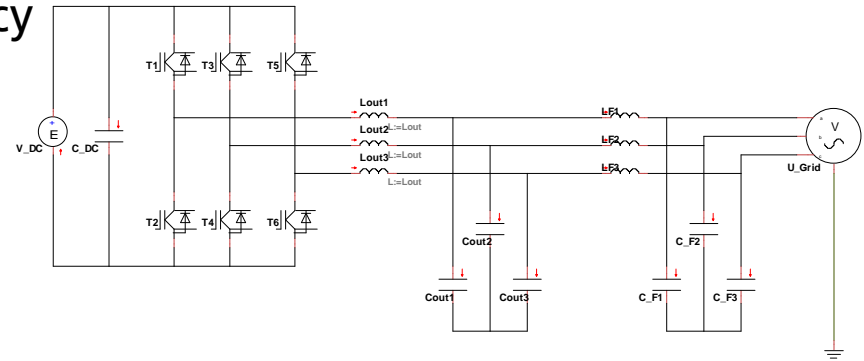
IZM Gen.2 (2015)
SiC MOSFets, 250 kHz pulse frequency
2,4l - 4 kg (15kW)
Embedded Power modules

Wie konnte so ein Fortschritt erreicht werden?



Schlüsselinnovationen in Gen 2

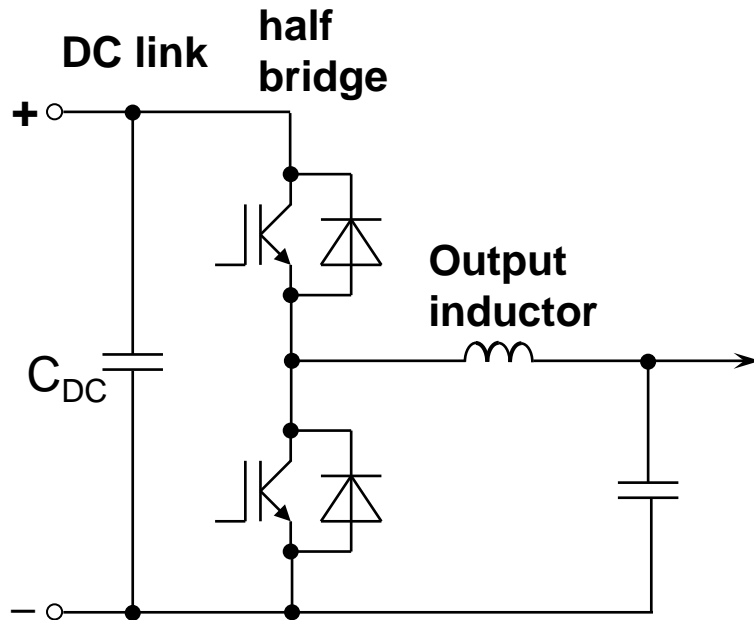
- Simple topology, high pulse frequency
- Semiconductor packaging
- Operation scheme
- Inductor design
- Filter design



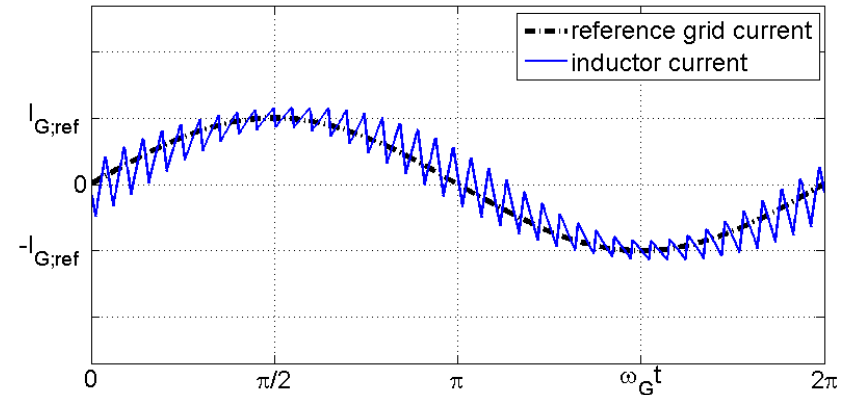
Schlüsselinnovationen in Gen 2

- Simple topology and high pulse frequency for low component number count
- Triangular current mode (TCM) for small output inductor and recovery of energy stored in semiconductor capacitance
- Variable pulse frequency to allow ZVS and reduce measured interference level
- Encapsulated EMI Semiconductor Packaging (EESP) to reduce EMI filter effort
- Revolutionary inductor design for output inductor
- High effort driver to accelerate SiC-Mosfets

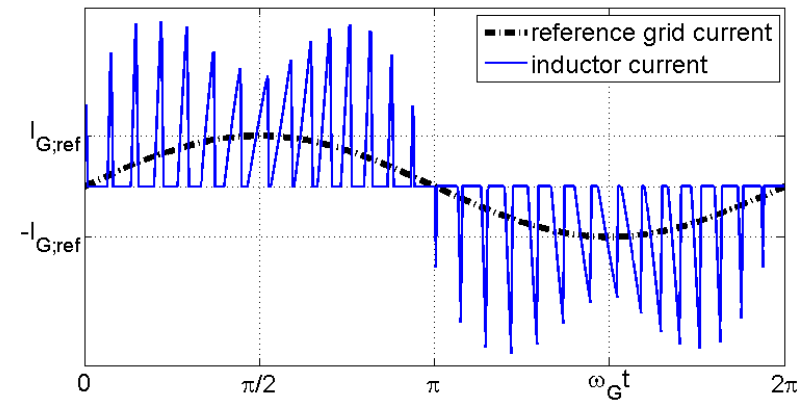
Schlüsselinnovationen in Gen 2



- Benefits of DCM in comparison with CCM
 - Inductance value is lower by a factor of app. 100 \rightarrow volume essentially lower
 - No semiconductor turn on losses

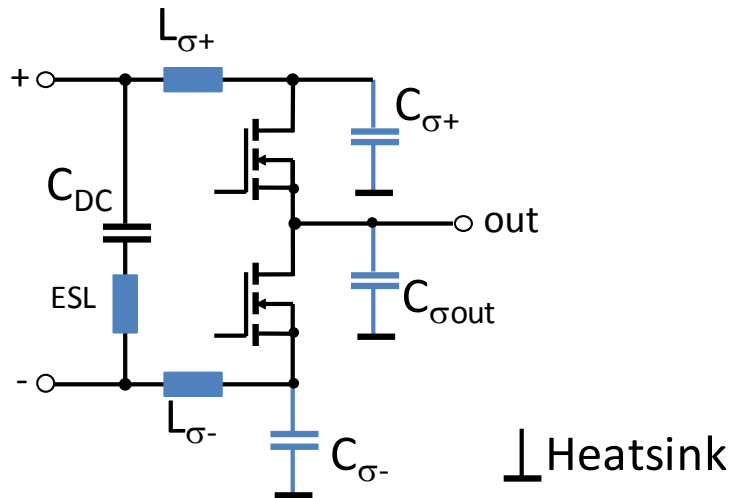


Discontinuous current mode DCM



Schlüsselinnovationen in Gen 2

The parasitics coming from the switching cell

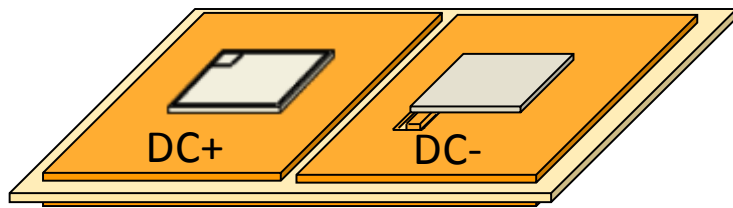


Which parameters are critical in the module?

- $L_{\sigma+}$, $L_{\sigma-}$ and ESL form the DC link inductance
- $C_{\sigma out}$ is reloaded with every switching event and originates a current in the heat sink -> EMC problems
- If C_{σ} or L_{σ} are unbalanced, a current into the heat sink is generated -> EMC problems

Schlüsselinnovationen in Gen 2

The Next Generation Package

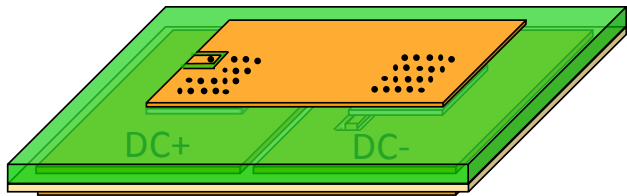


Solution:

- A ceramic substrate for safety insulation
- High and low side switch to complete the switching cell in the package
- DC+ and DC- lands with same size and geometry for balanced parasitics
- Low side chip flipped to avoid tracks carrying out potential

Schlüsselinnovationen in Gen 2

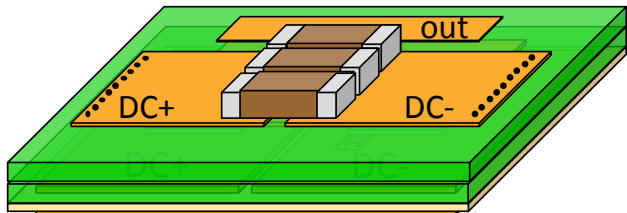
The Next Generation Package



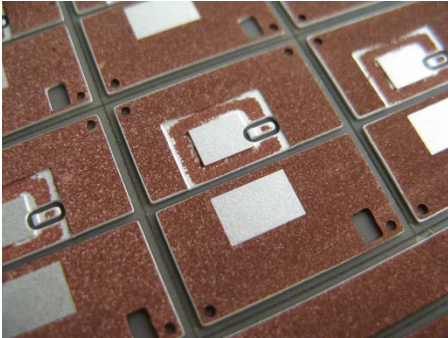
Next production steps:

- Embedding the chips in a PCB process and structuring the layer

- Surface layer with primary DC link capacitors and optional driver components



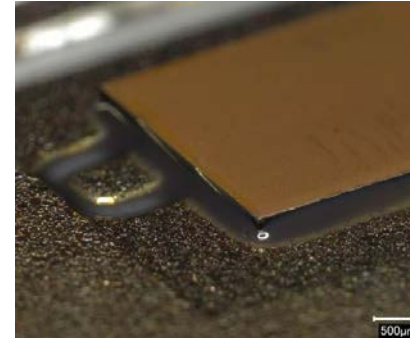
Schlüsselinnovationen in Gen 2



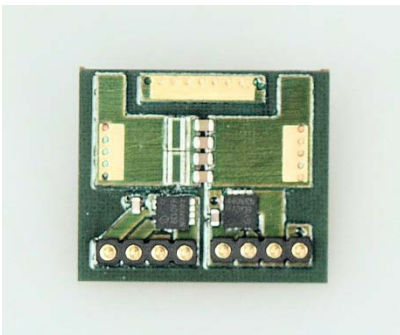
Silverpads on DCB



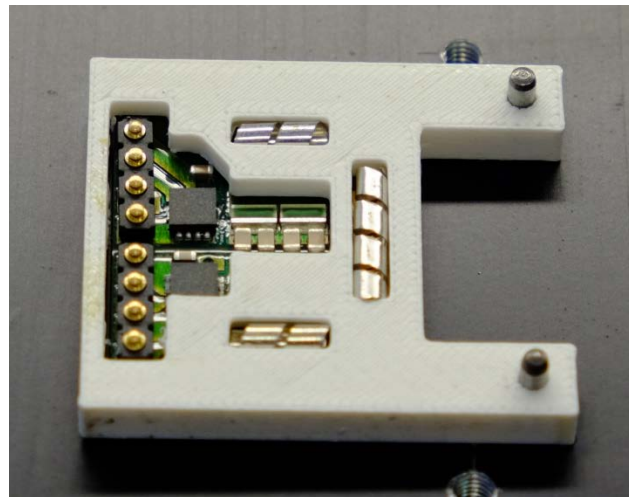
sintered chips



underfilled flip chip



final module

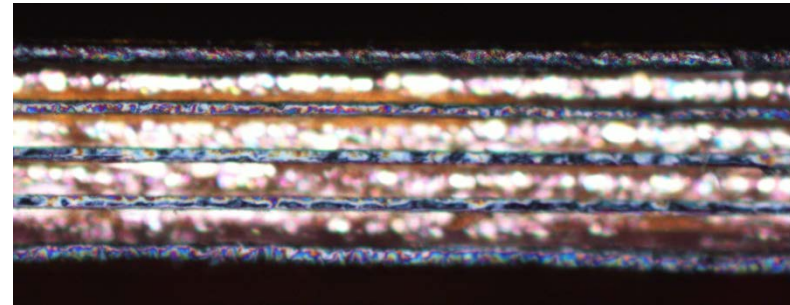
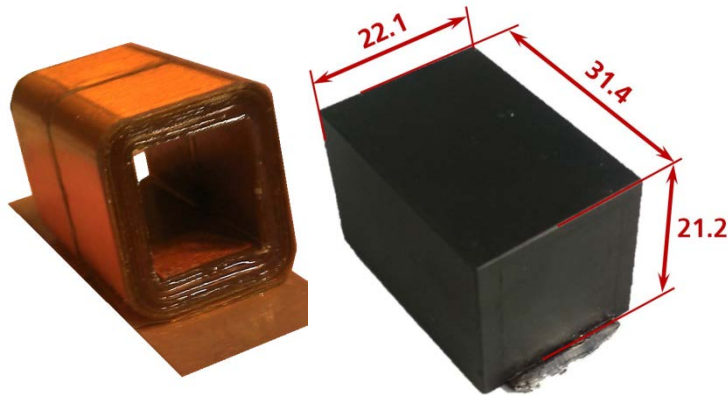
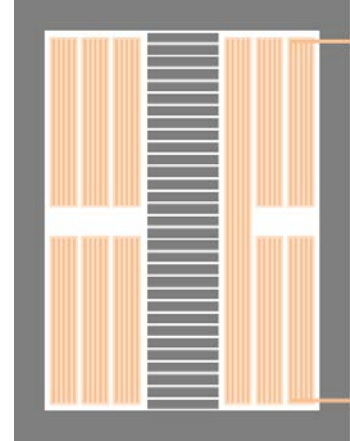


Module including plastic frame and springs

Schlüsselinnovationen in Gen 2

Completely altered design of inductors for high ripple+high frequency:

- high copper fill factor
- Skin&Proximity effect cancellation



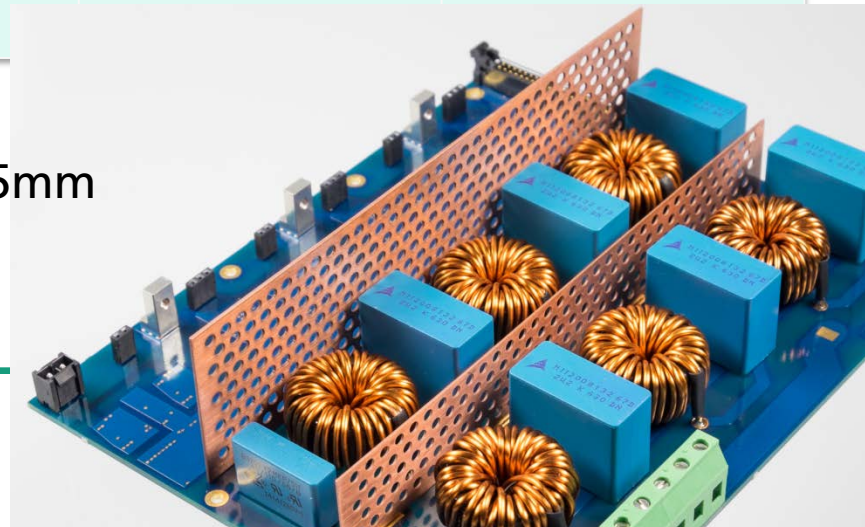
Foil stack with 22 μ m copper and 10 μ m insulation

Schlüsselinnovationen in Gen 2

- New EMI filtering concept

| | State of the art | SOLar | VFS |
|---|------------------|-----------------|-----------------|
| Switching frequency | 16kHz | 48kHz | 250kHz |
| Number of voltage levels | 3 | 3 | 2 |
| First frequency that has to be filtered f_1 | 160kHz | 192kHz | 250kHz |
| Limit value | 55.5dB μ V | 54.0dB μ V | 51.8dB μ V |
| Noise voltage @ $U_{DC}=650V$ and f_1 | 143.3dB μ V | 151.3dB μ V | 169.3dB μ V |
| Required filter attenuation @ f_1 | 87.8dB | 97.3dB | 117.5dB |

- 2 DM filter stages required
- Filter dimensions $l=107mm$, $b=98mm$, $h=35mm$



Aktuelle Generation 3

Fraunhofer IZM and **ETH** joined

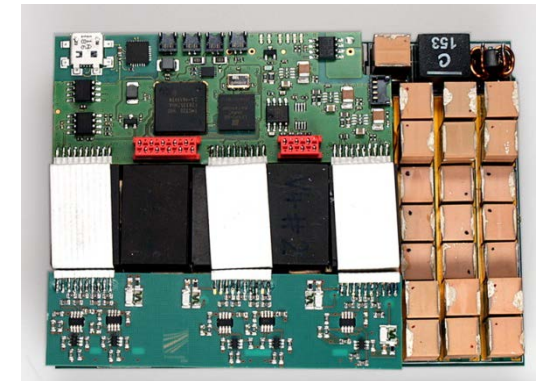
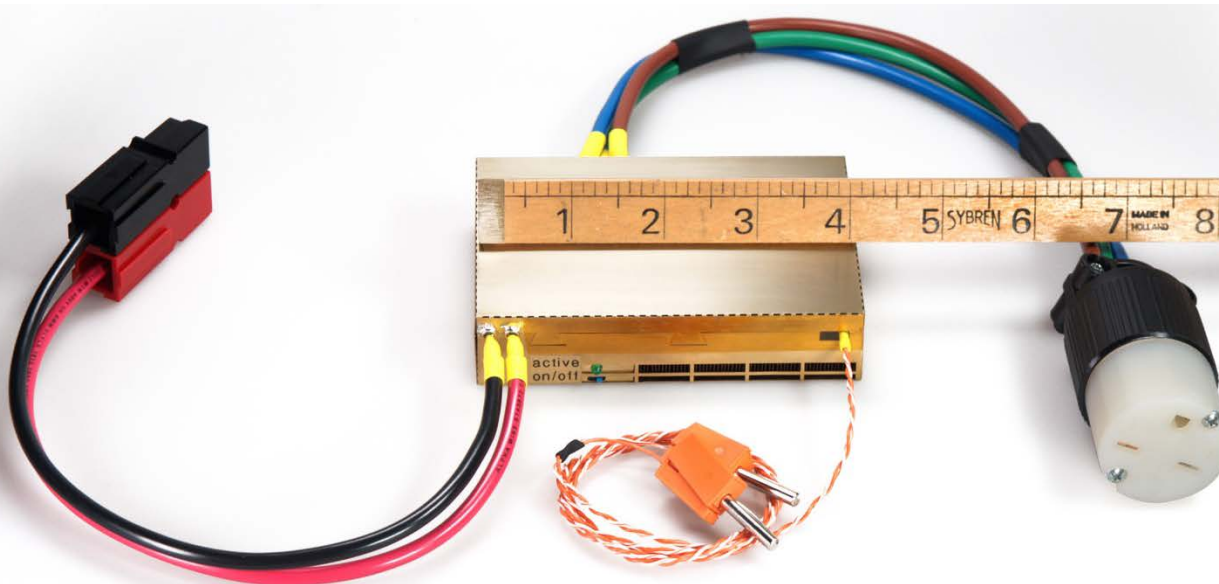


IZM Gen.3 (10/2015)

>300kHz

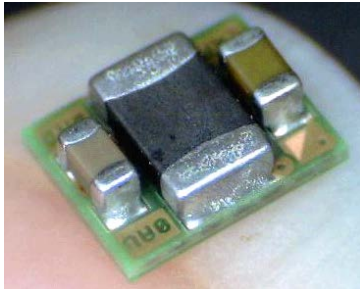
0,23l (2kW)

Innovation in topology, packaging, passive components, control

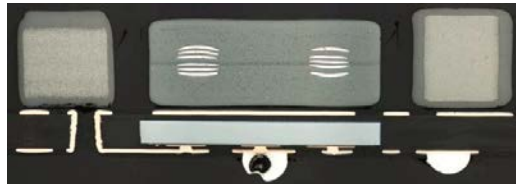


Heterogeneous Integration as next step

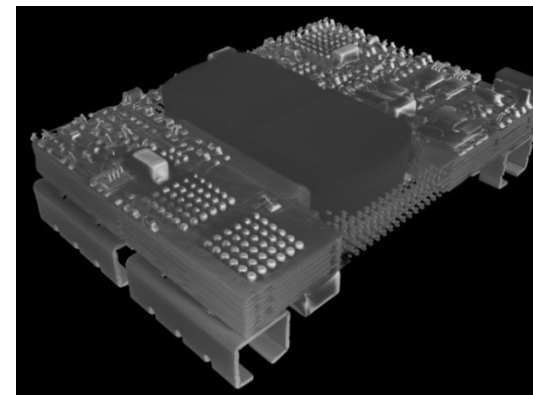
Two examples giving an idea on future development



 TEXAS INSTRUMENTS



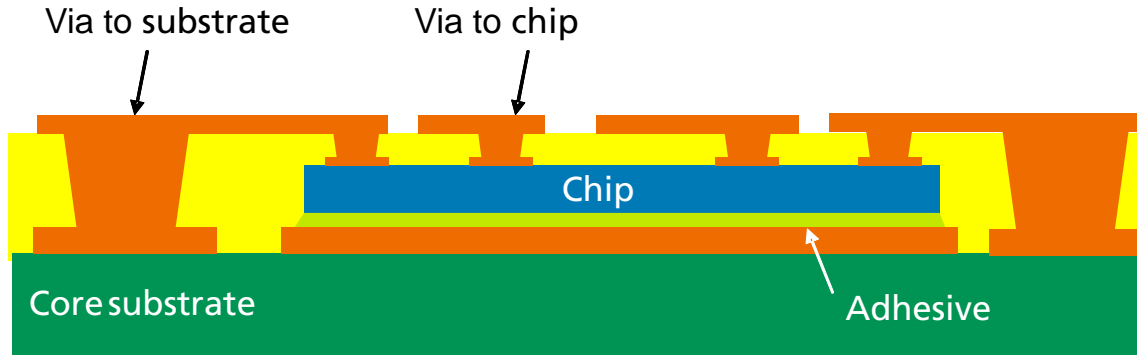
PCB with embedded
semiconductors and
SMD passives



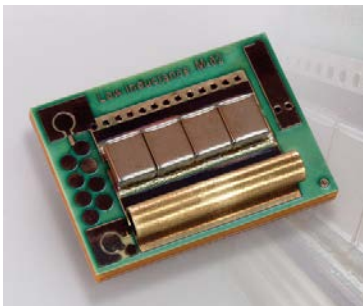
Multilayer PCB including
coil windings, overmolded

Heterogeneous Integration as next step

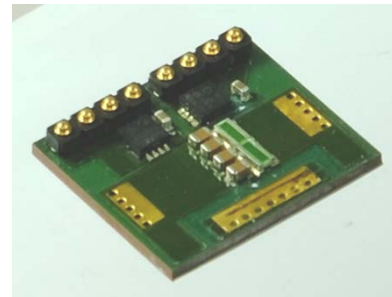
Embedding technologies



Examples for power modules in embedding on ceramic technology by IZM



1200V, 30A, world record in DC link: <math><1\text{nH}</math>

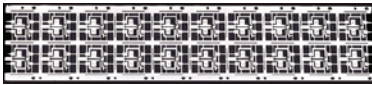


Heterogeneous Integration as next step

What is the benefit of embedding?

- Space saving on the PCB
- More freedom to design the electromagnetic parasitics beneficially
- Big production batches

Manufacturing on leadframes

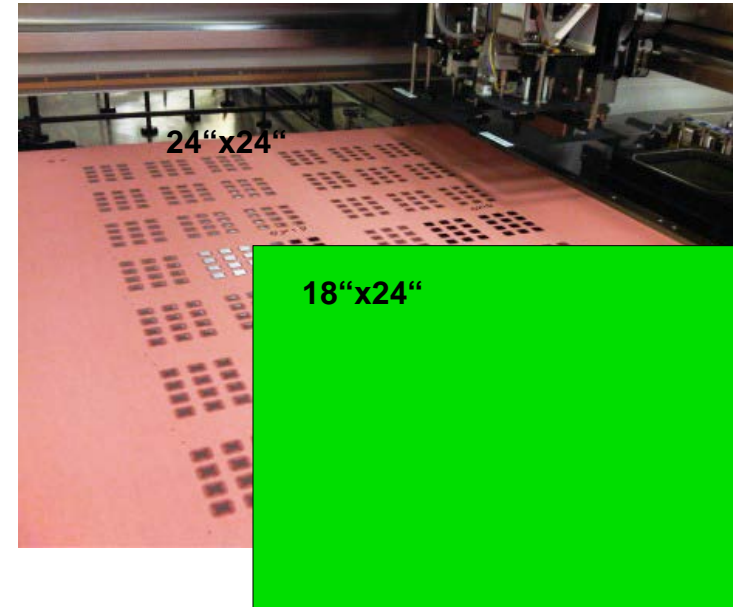


8"

~ 155 cm²

- **dominating technology**
 - many process options
 - cost optimised
- **OSAT**

Chip embedding in substrates

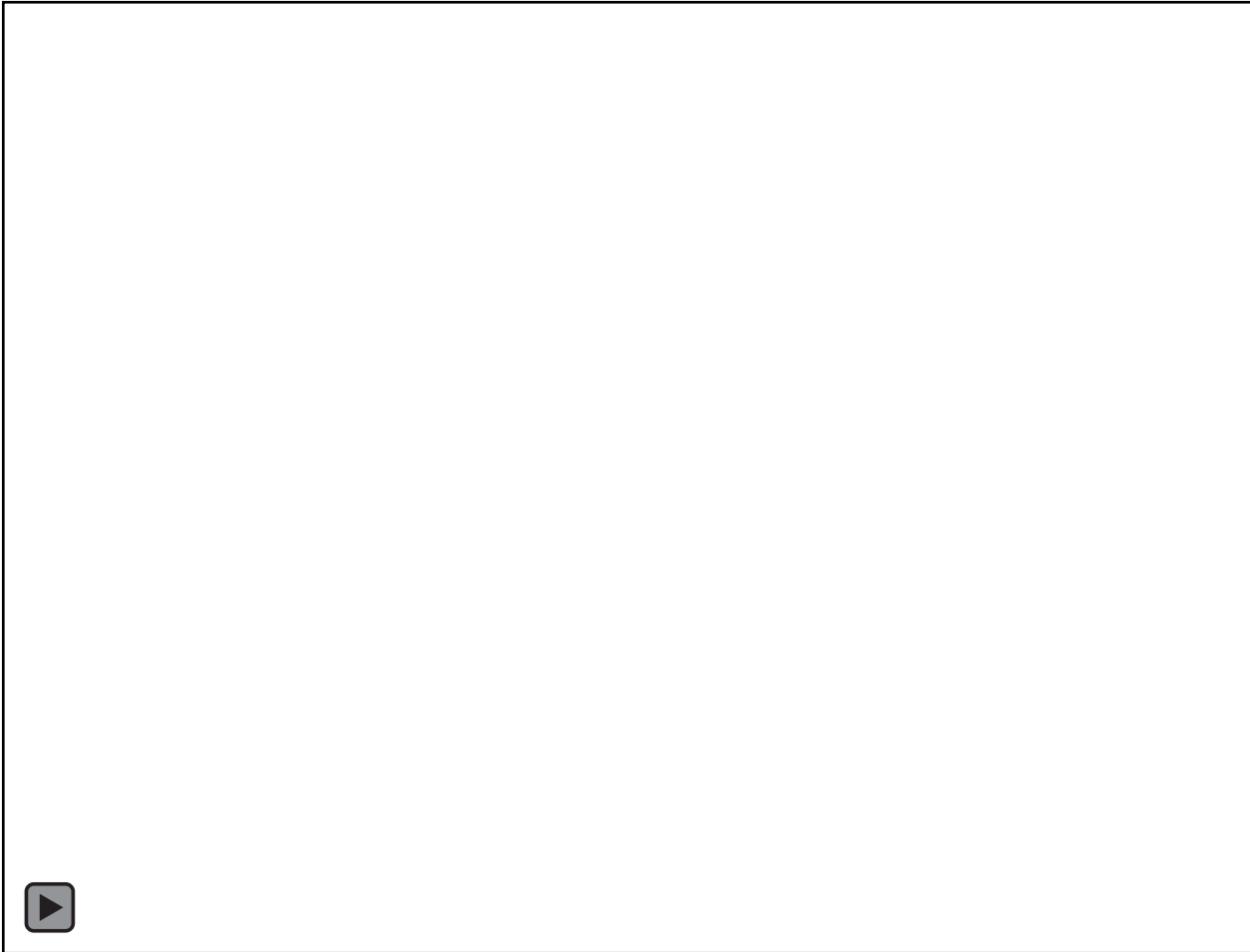


~ 2790 cm²

- **PCB technology**
 - begin of production
 - today low I/O chips
 - intrinsic 3D and power capability
- **PCB manufacturers**

Heterogeneous Integration as next step

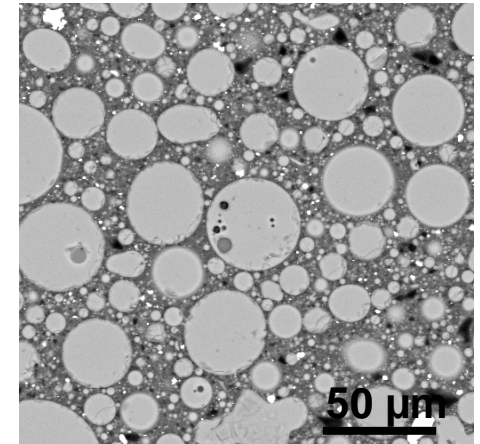
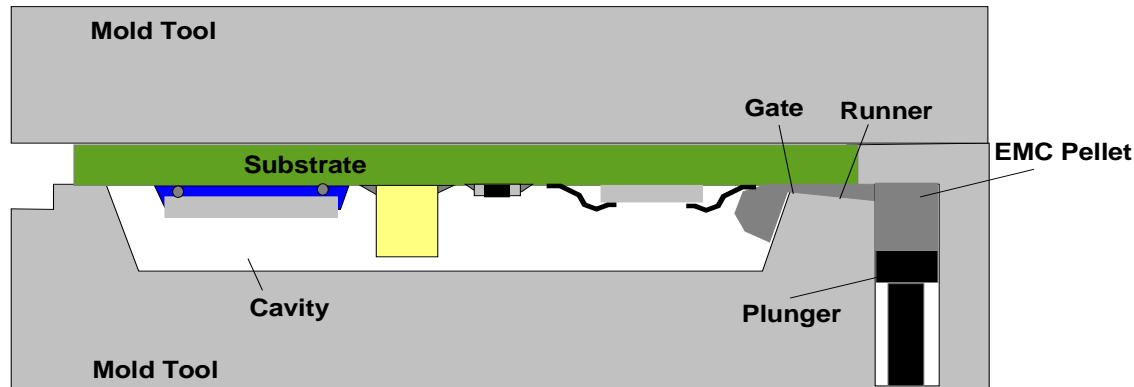
PSiP: Power System in package



- Power ratings up to 1.8kW in 8 cm³
- Multi layer PCB also used for coils
- SMD or bare die assembly
- Transfer Mold encapsulation for thermal and handling reasons

Heterogeneous Integration as next step

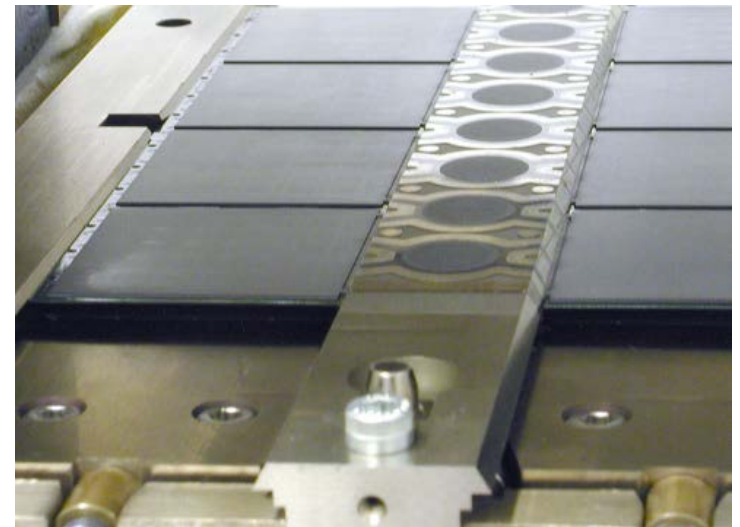
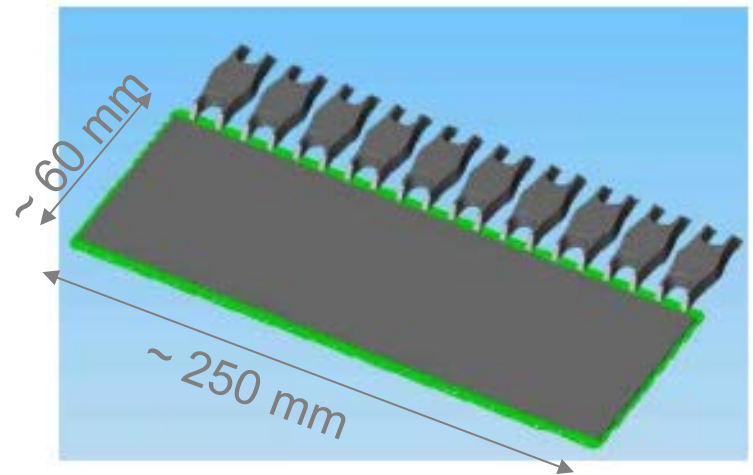
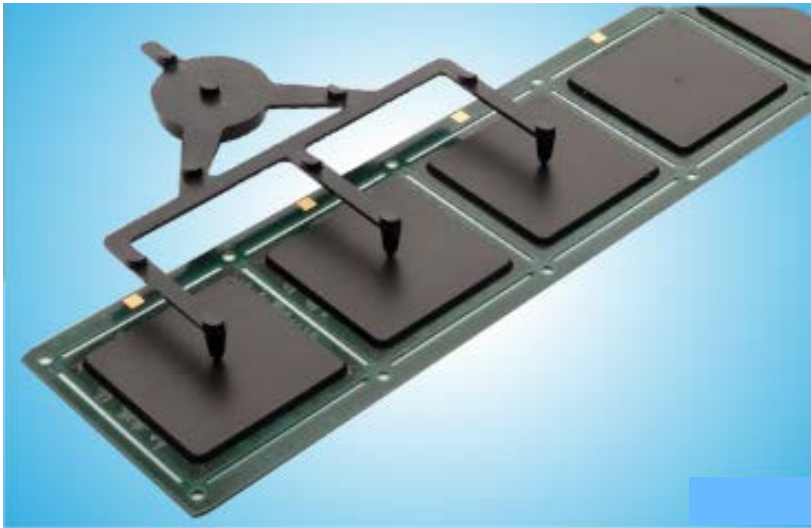
Transfer Mold Technology



SiO₂-filled epoxy resin

- Process Temp.: 160 – 180 °C
- Pressure: 50 - 150 bar
- Cycle Time: 1 - 2 min + 4h
- EMC: pellets
- Encapsulation: single & double sided
- Substrates: leadframe, PCB, DCB

Pin / Top Gate - Batchsize



Source: ASM

Source: Fico

Promising Technologies

What has to be packed in a PSiP (DC/DC converter)?

- Semiconductors (volume ~3%)
- Inductors -> ferrite (volume ~20%)
- Capacitors -> ceramics (volume ~10%)
- Conductors -> copper (~15%)
- Control, drivers, sensors (~12%)
- Insulation and unused volume (~40%)

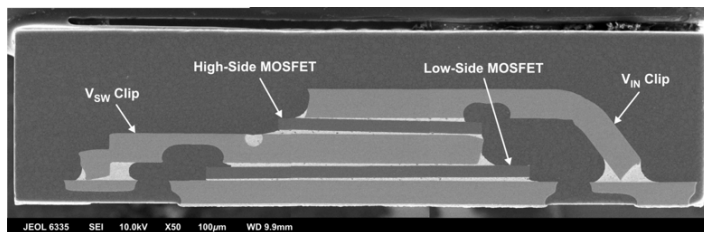
-> especially the ceramic materials are a nightmare in thermomechanical properties

Promising Technologies

How to bring these different components together?

Electrical interconnect: **Solder** Wire bond glued
 sintered Galvanic copper Transient liquid phase bond

- Soldering is the only standardized technology, where all components are prepared for
- Galvanic copper is used in the PCB manufacturing process, if beneficial it can also be used for semiconductor interconnects
- Wire bonds are well established for semiconductors
- Sintering can be used for semiconductors



Cross section of a TI power stack with two chips soldered upon each other

Promising Technologies

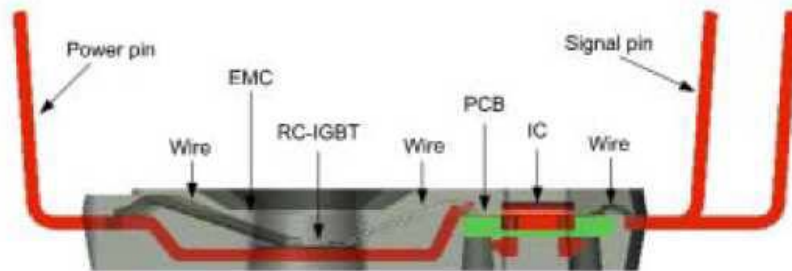
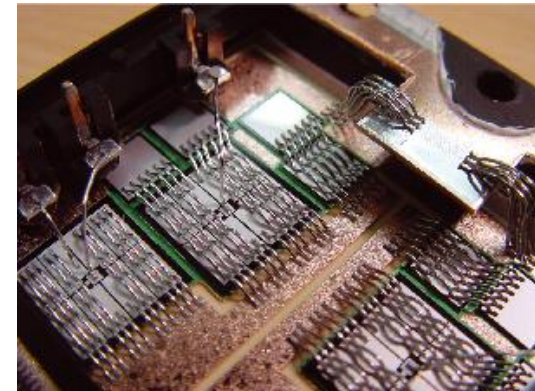
How to bring these different components together?

Substrate/carrier:

PCB
DCB
LEAD FRAME

Insulated metal
substrate

- PCB allows a high complexity interconnects and additionally medium quality inductor windings
- Direct Copper Bond has the best thermal conductivity for a required insulation
- Lead frame is cheap but low complexity



Promising Technologies

How to bring these different components together?

Encapsulation: **Transfer/Compression Mold**
Plastic frame+Silicone

- Transfer Mold encapsulation enables robust *Systems in Package* and can improve reliability and thermal properties. Tooling and process ramp up is expensive
- Main advantage of plastic frame and silicone is flexibility for customized solutions

Promising Technologies

What are the promising technologies to **Power Systems in Package**?

- Carrying substrate and electrical interconnection: PCB
higher number of interconnections compared to lead frame and wire bond, inductor manufacturing
Future issues: *thermal performance*
- Electrical and mechanical component assembly: soldering
all components are available for soldering, the variety of components requires an universal technology
- Encapsulation: Transfer/Compression mold
enables environmental and handling protection, thermal improvement
Future issues: *flexibility/package standardization*
- Chip interconnection: galvanic deposition in PCB process
is already part of the production process, embedded chips save space
Future issues: *availability of copper metalized chips*

Resume

What are future research tasks?

- Optimizing power electronics development towards packaging requirements
- Building up experience on material and process knowledge to allow the integration of these heterogeneous components
- Qualifying the processes
- Identifying products with sufficient high production numbers to recover the development costs

-> a lot of work...